NSN 5961-01-084-3002

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View Online at https://aerobasegroup.com/nsn/5961-01-084-3002 **Inclosure Material:** Metal **Overall Length:** 0.460 inches **Overall Diameter:** 0.610 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact-darlington connected Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-61 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Threaded stud **Features Provided:** Hermetically sealed case **Overall Width Across Flats:** 0.687 inches **Thread Size:** 0.250 inches **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 400.0 breakdown voltage, collector-to-emitter, base open and 500.0 breakdown voltage, collector-to-base, emitter open and 8.0 breakdown voltage, emitter-to-base, collector open **Current Rating Per Characteristic:** 20.00 amperes source cutoff current and 2.50 amperes source cutoff current **Power Rating Per Characteristic:** 100.0 watts small-signal input power, common-collector absolute **Special Features:** Junction pattern arrangement: pnp **Thread Series Designator:** Unf **Terminal Type And Quantity:** 3 tab, solder lug Shelf Life: N/a **Unit Of Measure:**

No

Demilitarization:

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